

# **BUK9Q20-40H**

# Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

28 August 2025

**Product data sheet** 

# 1. General description

Logic level N-Channel MOSFET in a compact MLPAK33-WF (SOT8002-3D) package using Trench 9 technology. This product has been designed and qualified to meet AEC-Q101 requirements delivering high performance and reliability.

### 2. Features and benefits

- Trench 9 technology Designed for ruggedness
- Small footprint (3 x 3 mm) for compact design
- Qualified to AEC-Q101 at 175 °C
- · Side-wettable flanks for robust solder joints and automated optical inspection

# 3. Applications

- Motor drive
- Battery protection
- · DC-DC conversion

# 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	28	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	30	W
Static charac	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		11.7	16.7	20	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 4.5 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 13; Fig. 14$		-	1	2	nC



Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4 — <u> </u>	
2	S	source		D
3	S	source		
4	G	gate		<sub>G</sub> (LE本)
mb	D	Mounting base; connected to drain	MLPAK33-WF (SOT8002-3)	mbb076 S

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BUK9Q20-40H		plastic thermal enhanced surface mounted package with side-wettable flanks (SWF); mini leads; 8 terminals;pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-3			

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
BUK9Q20-40H	1NH

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	40	V
$V_{GS}$	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	30	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	28	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	-	20	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3	-	111	А
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	n diode		·	·	·
Is	source current	T <sub>mb</sub> = 25 °C	-	25	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	111	А

### Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche rugg	edness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 12.62 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 46 μs; Fig. 4	[1] [2]	-	15	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 40 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; Fig. 4$	[3]	-	22	A

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.
- [3] Protected by 100% test

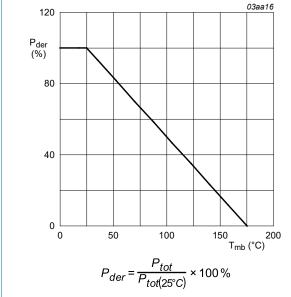


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

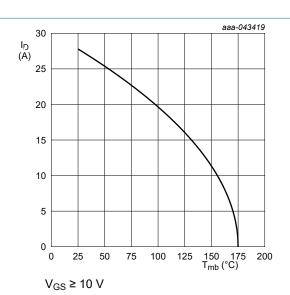
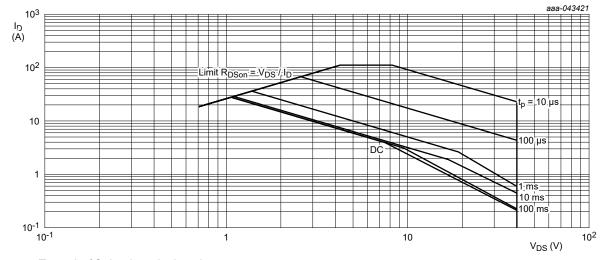


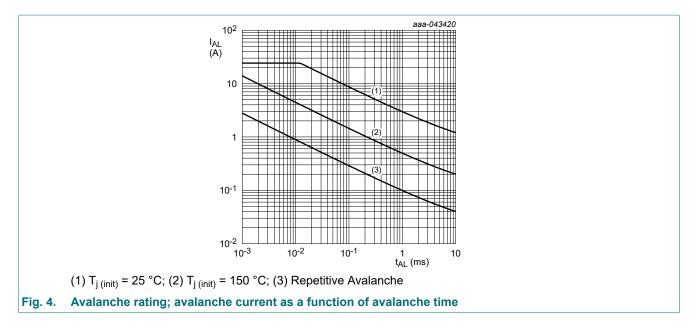
Fig. 2. Continuous drain current as a function of mounting base temperature



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

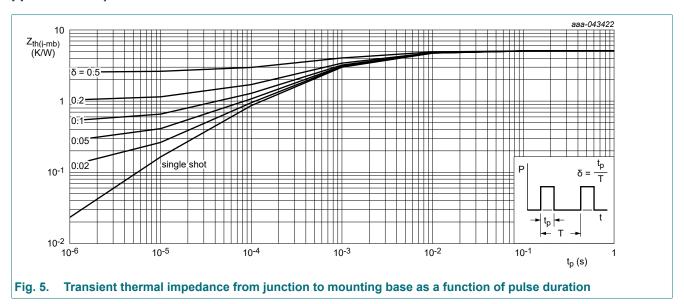


# 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5		-	4.24	5.08	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	-	-	40	K/W

[1] Device on 4 layer PCB. Refer to TN00008 for further information.



# Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

# 10. Characteristics

Table 7. Cha Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara		Conditions	141111	176	Mux	Oint
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	40	44		V
v (BR)DSS	breakdown voltage	$I_D = 250 \mu\text{A}, \text{Vgs} = 0 \text{V}, \text{I}_j = 25 \text{C}$ $I_D = 250 \mu\text{A}; \text{V}_{GS} = 0 \text{V}; \text{T}_i = -40 ^{\circ}\text{C}$	40	40.5		V
		$I_D = 250 \mu\text{A},  V_{GS} = 0  \text{V},  I_j = -40  \text{C}$ $I_D = 250 \mu\text{A};  V_{GS} = 0  \text{V};  T_i = -55  ^{\circ}\text{C}$	36	40.5	-	V
\/	gate-source threshold		1.35	1.75	2.05	V
V <sub>GS(th)</sub>	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.35	1.75	2.05	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.7	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$	-	-	2.6	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.01	1	μΑ
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	11.7	16.7	20	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 105 °C; Fig. 12	15.6	22	30	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 125 °C; Fig. 12	17	24	32	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12	20	29	38	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$	15	21.7	26	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 105 ^{\circ}\text{C};$ Fig. 12	20	27	39	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 12	22	30	42	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12	25	36	50	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>i</sub> = 25 °C	0.9	2.2	5.6	Ω
Dynamic ch	aracteristics	,				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V; T <sub>i</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	8.5	12	nC
		I <sub>D</sub> = 5 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 4.5 V;	-	4	5.6	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	1.5	2.3	nC
$Q_{GD}$	gate-drain charge		-	1	2	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	509	713	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	165	231	pF
C <sub>rss</sub>	reverse transfer capacitance		-	22	49	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 4 \Omega; V_{GS} = 4.5 \text{ V};$	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time	-	-	8	-	ns
t <sub>f</sub>	fall time		-	4		ns

### Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	13	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <u>Fig. 17</u>	[1]	-	6	-	nC

#### [1] includes capacitive recovery

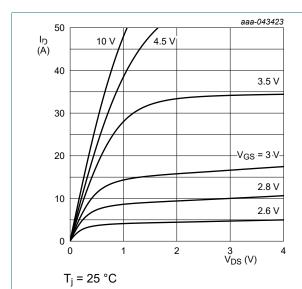


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

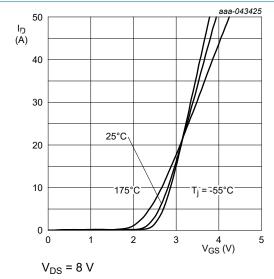


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

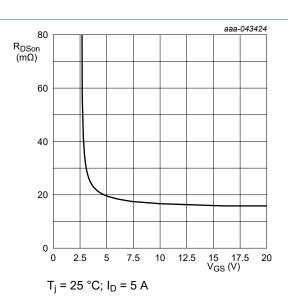


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

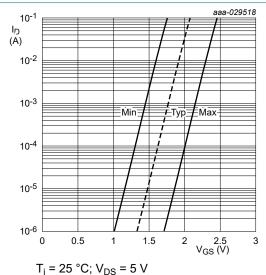


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

### Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

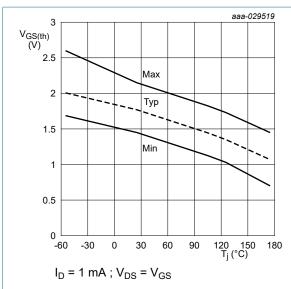


Fig. 10. Gate-source threshold voltage as a function of junction temperature

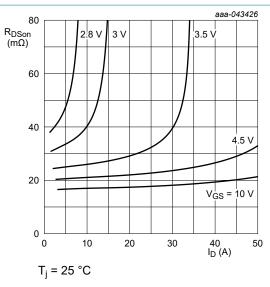


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

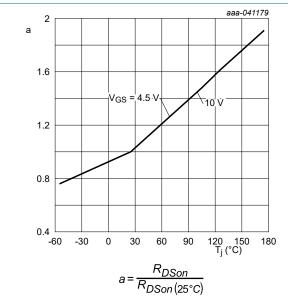


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

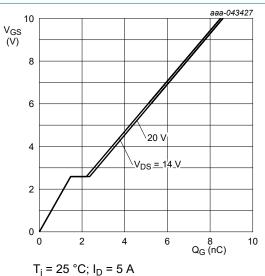


Fig. 13. Gate-source voltage as a function of gate charge; typical values

### Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

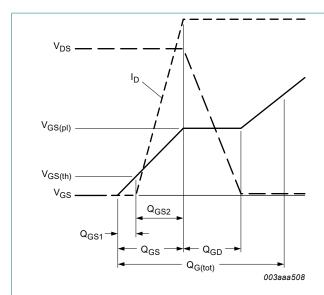
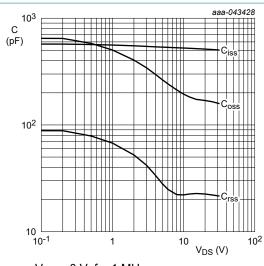


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V; f = 1 MHz$ 

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

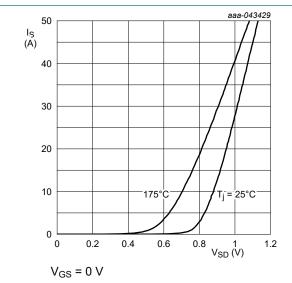


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

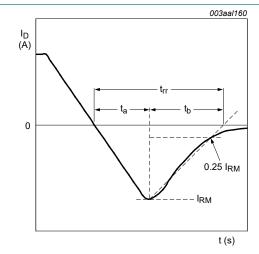


Fig. 17. Reverse recovery timing definition

### Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

# 11. Package outline

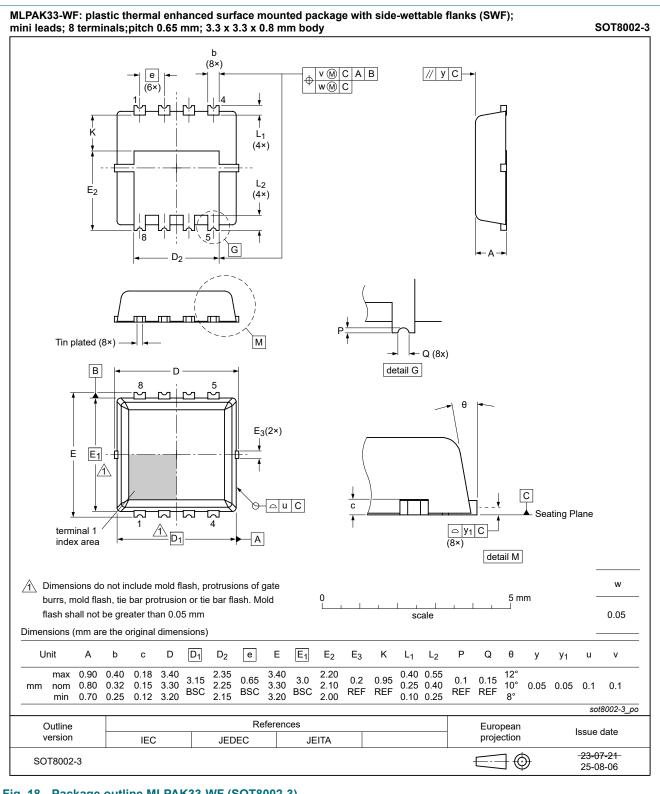
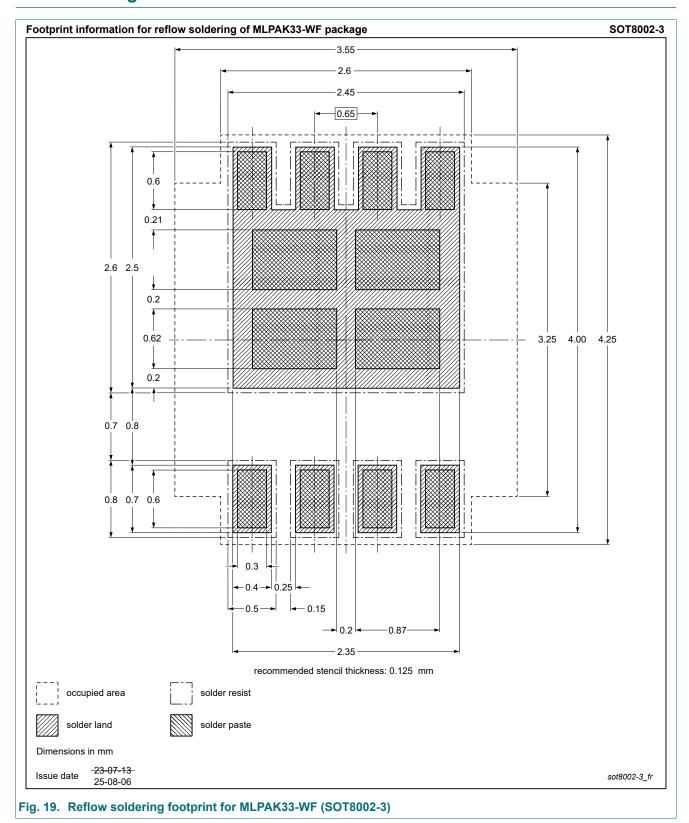


Fig. 18. Package outline MLPAK33-WF (SOT8002-3)

Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

# 12. Soldering



### Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

# 13. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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# Logic level N-Channel MOSFET in MLPAK33-WF (SOT8002-3D)

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